

FAST [2456.wsp.1]

File View Edit Tools Window Help

Active

- L4: (10148) (etch\$3 with ('HCl' hydrogen adj chloride hydrochloric))
- L5: (491) 4 and (plasma with ('HCl' hydrogen adj chloride hydrochloric))
- L6: (48) 5 and (plasma with (ferromagnetic magnetic magneticresistive magnetization))
- L7: (46) 5 and (etch\$3 with (ferromagnetic magnetic magneticresistive magnetization))
- L8: (41) 6 and 7
- L9: (41) 8 and (etch\$3 'HCl' hydrogen adj chloride hydrochloric)
- L10: (41) 9 and (plasma ferromagnetic magnetic magneticresistive magnetization)
- L11: (36) 10 and (plasma with (chamber reactor))
- L12: (11) 11 and ((layer material) with (ferromagnetic magnetic magneticresistive magnetization))**

Failed

- (0) 63 and ('HCl' hydrogen adj chloride hydrochloric)

Saved

- (1529) (plasma with ('HCl' hydrogen adj chloride hydrochloric))
- (737) plasma with (nonferromagnetic antiferromagnetic non-ferromagnetic nonmagnetic non-magnetic)
- (16722) plasma with (ferromagnetic magnetic magnetic magneticresistive magnetization)
- (17) (((plasma with ('HCl' hydrogen adj chloride hydrochloric)) and ((plasma with ('HCl'

11 and ((layer material) with (ferromagnetic magnetic magneticresistive magnetization))

	U	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	US 20030170985	20030911	11	Etching methods for a magnetic memory cell stack	438/689	
2	<input type="checkbox"/>	US 20030104697	20030605	9	Dry clean method instead of traditional wet clean after metal etch	438/689	134/1.3
3	<input type="checkbox"/>	US 20020142572	20021003	45	Method for forming metallic film and apparatus for forming the same	438/586	257/E21.17; 438/584
4	<input type="checkbox"/>	US 6526996 B1	20030304	8	Dry clean method instead of	134/1.3	134/1.2;

Hit Details HTML

Ready